

Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, Ca 90638 Phone: (562) 404-4474 * Fax: (562) 404-1773 ssdi@ssdi-power.com * www.ssdi-power.com

DESIGNER'S DATA SHEET

SHF12

Screening 2/ = Not Screened $\overline{TX} = TX \text{ Level}$ TXV = TXVS = S Level

Package Type

= Axial Leaded $\overline{SMS} = Surface Mount Square Tab$

Family/Voltage

04 = 400 V06 = 600 V08 = 800 V

09 = 900 V

SHF1204 & SHF1204SMS thru **SHF1209 & SHF1209SMS**

2 AMP 400 - 900 V **Hyper Fast Rectifier**

Features:

- Hyper Fast Recovery: 40 nsec maximum
- PIV to 900 Volts, Consult Factory
- · Hermetically Sealed
- Void Free Construction
- For High Efficiency Applications
- Replaces UES1204, UES1206
- TX, TXV, S Level screening Available^{2/}

Maximum Ratings			Symbol	Value	Units
Peak Repetitive Reverse and DC B	locking Voltage	SHF1204 SHF1206 SHF1208 SHF1209	$egin{array}{c} V_{RRM} \ V_{RSM} \ V_{R} \end{array}$	400 600 800 900	Volts
Average Rectified Forward Currer (Resistive Load, 60 hz Sine Wave, T			Io	2.0	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave, T _A =	25 °C)		I_{FSM}	20	Amps
Operating & Storage Temperature	2		T _{OP} & T _{STG}	-65 to +175	°C
Maximum Thermal Resistance	Junction to Le Junction to Tab	,	$R_{ heta JL} \ R_{ heta JE}$	35 28	°C/W

NOTES:

1/ For Ordering Information, Price, and Availability- Contact Factory.

2/ Screening Based on MIL-PRF-19500. Screening Flows Available on Request.

Axial Lead Diode

SMS





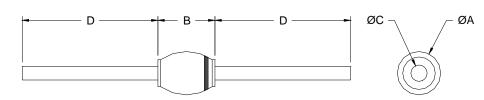
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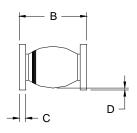
Electrical Characteristic	Symbol	Max	Units
Instantaneous Forward Voltage Drop (I _F = 1.2A _{DC} , T _A = 25°C; pulsed)	$\mathbf{V_F}$	1.7	$V_{ m DC}$
Instantaneous Forward Voltage Drop (I _F = 2A _{DC} , T _A = 25°C; pulsed)	V_{F}	1.9	$ m V_{DC}$
Reverse Leakage Current (Rated V_R , $T_A = 25$ °C; pulsed)	I_R	10	μΑ
Reverse Leakage Current (Rated V_R , $T_A = 100$ °C; pulsed)	I_R	1	mA
Junction Capacitance (V _R =10V _{DC} , T _A =25°C, f=1MHz)	$C_{ m J}$	22	pF
Reverse Recovery Time $(I_F = 500 \text{mA}, I_R = 1 \text{A}, I_{RR} = 250 \text{mA}, T_A = 25^{\circ}\text{C})$ $(I_F = 500 \text{mA}, I_R = 1 \text{A}, I_{RR} = 250 \text{mA}, T_A = 100^{\circ}\text{C})$	$t_{ m RR}$	40 80	nsec

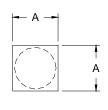




DIM	MIN	MAX
A	0.100"	0.130"
В	0.130"	0.180"
C	0.027"	0.033"
D	1.00"	

Case Outline: (SMS)





DIM	MIN	MAX
A	0.127"	0.140"
В	0.180"	0.230"
C	0.020"	0.030"
D	0.002"	